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APPENDIX

LIST OF PUBRICATIONS

1. International Journals and International Conferences

1. **Wipakorn Jevasuwan**; Supachok Thainoi; Songphol Kanjanachuchai; Somchai Ratanathamphan; and Somsak Panyakeow. 2006. InAs and InP Quantum Dot Molecules and their Potentials for Photovoltaic Applications. Proceedings of Material Research Society Fall Meeting 194.
2. **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2007. InP Ring-like Nanostructures on $\text{In}_{0.49}\text{Ga}_{0.51}\text{P}$ Grown by Droplet Epitaxy. Proceedings of the 2nd IEEE International Conference on Nano/Micro Engineered and Molecular Systems 151.
3. **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2007. In-droplet-induced Formation of InP Nanostructures by Solid-source Molecular-beam Epitaxy. Microelectronic Engineering 84: 1548-1551.
4. **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2007. The Formation of InP Ring-shape Nanostructures on $\text{In}_{0.49}\text{Ga}_{0.51}\text{P}$ Grown by Droplet Epiatxy. Advanced Materials Research 31: 158-160.
5. Poonyasiri Boonpeng; **Wipakorn Jevasuwan**; Suwaree Suraprapapich; Somchai Ratanathamphan; and Somsak Panyakeow. 2009. Quadra-Quantum Dots Grown on Quantum Rings Having Square-Shaped Holes: Basic Nanostructure for Quantum Dot Cellular Automata Application. Microelectronic Engineering 86: 853-856.
6. **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2009. Dependency of In Thickness on the Properties of Self-assembled InP ring-shape Nanostructures Grown by Droplet Molecular Beam Epitaxy. Proceedings of the 5th International Conference on Materials for Advanced Technologies 23-24.

7. Poonyasiri Boonpeng; **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2009. Fabrication of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ (001) Nanohole Templates Grown by Droplet Molecular Beam Epitaxy. Proceedings of the International Conference on Nanoscience and Technology, China 2009 447.
8. **Wipakorn Jevasuwan**; Poonyasiri Boonpeng; Somsak Panyakeow; and Somchai Ratanathamphan. 2009. InP Ring-shaped Quantum-dot Molecules Grown by Droplet Molecular Beam Epitaxy. Proceedings of 2009 International Conference on Solid State Devices and Materials 830-831.
9. **Wipakorn Jevasuwan**; Poonyasiri Boonpeng; Somsak Panyakeow; and Somchai Ratanathamphan. 2010. Growth and Characterization of InP Ringlike Quantum-dot Molecules Grown by Solid-source Molecular-beam Epitaxy. Journal of Nanoscience and Nanotechnology 10: 1-4.
10. **Wipakorn Jevasuwan**; Poonyasiri Boonpeng; Somsak Panyakeow; and Somchai Ratanathamphan. 2010. Influence of Crystallization Temperature on InP Ring-Shaped Quantum-Dot Molecules Grown by Droplet Epitaxy. Microelectronic Engineering 87: 1416-1419.
11. Poonyasiri Boonpeng; **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2010. Fabrication of $\text{In}_{0.15}\text{Ga}_{0.85}\text{As}$ Nanohole Templates on GaAs (001) for Quantum dot Molecules. Japan Journal of Applied Physics 49: *In Press*.

2. Domestic Journals and Domestic Conferences

1. **Wipakorn Jevasuwan**; Poonyasiri Boonpeng; Pornchai Changmoang; Supachok Thainoi; Somsak Panyakeow; and Somchai Ratanathamphan. 2007. Study and Fabrication of InP Nanostructures by Droplet Molecular Beam Epitaxy. Proceedings of the 30th Electrical Engineering Conference 2: 1285-1288.
2. **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2008. InP ring-shape Nanostructures on $\text{In}_{0.49}\text{Ga}_{0.51}\text{P}$ Grown by Droplet Epitaxy. Proceedings of RGJ-Ph.D. Congress IX 237.
3. **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamphan. 2008. The Effect of In Deposition Rate on the Properties of InP Nanostructures Grown by Droplet Molecular Beam Epitaxy. Proceedings of the 31st Electrical Engineering Conference 2: 1031-1034.
4. **Wipakorn Jevasuwan**; Supachok Thainoi; Pornchai Changmoang; Somsak Panyakeow; and Somchai Ratanathamphan. 2009. The Effect of In Thickness on the Properties of InP ring-shape Quantum-dot Molecules Grown by Droplet Molecular Beam Epitaxy. Proceedings of RGJ-Ph.D. Congress X 233.
5. **Wipakorn Jevasuwan**; Poonyasiri Boonpeng; Pornchai Changmoang; Supachok Thainoi; Noppadon Nuntawong; Somsak Panyakeow; and Somchai Ratanathamphan. 2009. InP Ring-shaped Quantum-dot Molecules for Extended Quantum-dot Cellular Automata. Proceedings of the 32nd Electrical Engineering Conference 2: 1179-1182.
6. Poonyasiri Boonpeng; **Wipakorn Jevasuwan**; Pornchai Changmoang; Supachok Thainoi; Somsak Panyakeow; and Somchai Ratanathamphan. 2009. Fabrication of $\text{In}_{0.15}\text{Ga}_{0.85}\text{As}$ Nanohole Templates on GaAs(001). Proceedings of the 32nd Electrical Engineering Conference 2: 1239-1242.

LIST OF PRESENTATIONS

1. International Presentations

- *Poster presentation*

Wipakorn Jevasuwan; Somsak Panyakeow; and Somchai Ratanathammaphan. 2007. In-droplet-induced Formation of InP Nanostructures by Solid-source Molecular-beam Epitaxy. The 32nd International Conference on Micro- and Nano-Engineering 2006 (MNE 2006), Barcelona, Spain, September 17-20 (2006).

- *Poster presentation*

Wipakorn Jevasuwan; Supachok Thainoi; Songphol Kanjanachuchai; Somchai Ratanathammaphan; and Somsak Panyakeow. InAs and InP Quantum Dot Molecules and their Potentials for Photovoltaic Applications. Material Research Society Fall Meeting (MRS Fall Meeting 2006), Boston, United States of America, November 27-December 1 (2006).

- *Poster presentation*

Wipakorn Jevasuwan; Somsak Panyakeow; and Somchai Ratanathammaphan. InP Ring-like Nanostructures on $\text{In}_{0.49}\text{Ga}_{0.51}\text{P}$ Grown by Droplet Epitaxy. The 2nd IEEE International Conference on Nano/Micro Engineered and Molecular Systems (IEEE-NEMS 2007), Bangkok, Thailand, January 16-19 (2007).

- *Poster presentation*

Wipakorn Jevasuwan; Somsak Panyakeow; and Somchai Ratanathammaphan. The Formation of InP Ring-shape Nanostructures on $\text{In}_{0.49}\text{Ga}_{0.51}\text{P}$ Grown by Droplet Epitaxy. The 4th International Conference on Materials for Advanced Technologies (ICMAT 2007), Singapore, Singapore, July 1-6 (2007).

- *Poster presentation*

Poonyasiri Boonpeng; **Wipakorn Jevasuwan**; Suwaree Suraprapapich; Somchai Ratanathamaphan; and Somsak Panyakeow. Quadra-Quantum Dots Grown on Quantum Rings Having Square-Shaped Holes: Basic Nanostructure for Quantum Dot Cellular Automata Application. The 34th International Conference on Micro- and Nano-Engineering 2008 (MNE 2008), Athens, Greece, September 15 -18 (2008).

- *Poster presentation*

Wipakorn Jevasuwan; Somsak Panyakeow; and Somchai Ratanathamaphan. Dependency of In Thickness on the Properties of Self-assembled InP ring-shape Nanostructures Grown by Droplet Molecular Beam Epitaxy. The 5th International Conference on Materials for Advanced Technologies (ICMAT 2009), Singapore, Singapore, June 28-July 3 (2009). (*Best Poster Award*)

- *Poster presentation*

Wipakorn Jevasuwan; Poonyasiri Boonpeng; Somsak Panyakeow; and Somchai Ratanathamaphan. Growth and Characterization of InP Ringlike Quantum-dot Molecules Grown by Solid-source Molecular-beam Epitaxy. The International Conference on Nanoscience and Technology China 2009 (ChinaNANO 2009), Beijing, China, September 1-3 (2009).

- *Poster presentation*

Poonyasiri Boonpeng; **Wipakorn Jevasuwan**; Somsak Panyakeow; and Somchai Ratanathamaphan. Fabrication of $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ (001) Nanohole Templates Grown by Droplet Molecular Beam Epitaxy. The International Conference on Nanoscience and Technology China 2009 (ChinaNANO 2009), Beijing, China, September 1-3 (2009).

- *Poster presentation*

Wipakorn Jevasuwan; Poonyasiri Boonpeng; Somsak Panyakeow; and Somchai Ratanathammaphan. InP Ring-Shaped Quantum-Dot Molecules Formed by Droplet Epitaxy Grown by Solid-source Molecular Beam Epitaxy. Asia Nanotech Camp 2009 (ANC 2009), Taiwan, September 28- October 12 (2009). (*Best Poster Award*)

- *Poster presentation*

Wipakorn Jevasuwan; Poonyasiri Boonpeng; Somsak Panyakeow; and Somchai Ratanathammaphan. Influence of Crystallization Temperature on InP Ring-Shaped Quantum-Dot Molecules Grown by Droplet Epitaxy. The 35th International Conference on Micro- and Nano-Engineering 2009 (MNE 2009), Ghent, Belgium, September 28- October 1 (2009).

- *Poster presentation*

Poonyasiri Boonpeng; **Wipakorn Jevasuwan;** Somsak Panyakeow; and Somchai Ratanathammaphan. Fabrication of $\text{In}_{0.15}\text{Ga}_{0.85}\text{As}$ Nanohole Templates on GaAs (001) for Quantum dot Molecules. 2009 International Conference on Solid State Devices and Materials (SSDM 2009), Sendai, Japan, October 7-9 (2009).

- *Oral presentation*

Wipakorn Jevasuwan; Poonyasiri Boonpeng; Somsak Panyakeow; and Somchai Ratanathammaphan. InP Ring-shaped Quantum-dot Molecules Grown by Droplet Molecular Beam Epitaxy. 2009 International Conference on Solid State Devices and Materials (SSDM 2009), Sendai, Japan, October 7-9 (2009).

2. Domestic Presentations

- *Poster presentation*

Wipakorn Jevasuwan; Somsak Panyakeow; and Somchai Ratanathamphan. InP ring-shape Nanostructures on In_{0.49}Ga_{0.51}P Grown by Droplet Epitaxy. RGJ-Ph.D. Congress IX, Pattaya, Thailand, April 4-6 (2008).

- *Poster presentation*

Wipakorn Jevasuwan; Supachok Thainoi; Pornchai Changmoang; Somsak Panyakeow; and Somchai Ratanathamphan. The Effect of In Thickness on the Properties of InP ring-shape Quantum-dot Molecules Grown by Droplet Molecular Beam Epitaxy. RGJ-Ph.D. Congress X, Pattaya, Thailand, April 3-5 (2009).

- *Oral presentation*

Wipakorn Jevasuwan; Poonyasiri Boonpeng; Pornchai Changmoang; Supachok Thainoi; Somsak Panyakeow; and Somchai Ratanathamphan. Study and Fabrication of InP Nanostructures by Droplet Molecular Beam Epitaxy. The 30th Electrical Engineering Conference (EECON 30), Kanchanaburi, Thailand, October 25-26 (2007).

- *Oral presentation*

Wipakorn Jevasuwan; Somsak Panyakeow; and Somchai Ratanathamphan. 2008. The Effect of In Deposition Rate on the Properties of InP Nanostructures Grown by Droplet Molecular Beam Epitaxy. The 31st Electrical Engineering Conference (EECON 31), Nakhonnayok, Thailand, October 29-31 (2008).

- *Oral presentation*

Wipakorn Jevasuwan; Poonyasiri Boonpeng; Pornchai Changmoang; Supachok Thainoi; Noppadon Nuntawong; Somsak Panyakeow; and Somchai Ratanathamphan. InP Ring-shaped Quantum-dot Molecules for Extended Quantum-dot Cellular Automata. The 32nd Electrical Engineering Conference (EECON 32), Phachinburi, Thailand, October 28-30 (2009). (*Best Paper Award*)

- *Oral presentation*

Poonyasiri Boonpeng; **Wipakorn Jevasuwan**; Pornchai Changmoang; Supachok Thainoi; Somsak Panyakeow; and Somchai Ratanathamphan. 2009. Fabrication of In_{0.15}Ga_{0.85}As Nanohole Templates on GaAs(001). The 32nd Electrical Engineering Conference (EECON 32), Phachinburi, Thailand, October 28-30 (2009).

VITAE

Wipakorn Jevasuwan was born in Lopburi, Thailand on July 22, 1981. She graduated in high school education from Satriwittaya II School. In June 1998, she entered Kasetsart University and received the Bachelor of Engineering in Electrical Engineering Program in March 2002.

In November 2002, she entered the Graduate School of Chulalongkorn University and became the Master degree's student in Electrical Engineering Program at Semiconductor Devices Research Laboratory (SDRL). She received the Master degree of Engineering in Electrical Engineering Program in May 2005 and further studied as a Ph.D. student in Electrical Engineering Program at the same laboratory. Her work is financial supported by the Thailand Research Fund (TRF) through the Royal Golden Jubilee (RGJ) Scholarship.

Between September 2007 and December 2007, she received the Toshiba International Foundation (TIFO) Scholarship and worked as a visiting student in Electron Devices Laboratory, Toshiba Corporate Research & Development Center, Toshiba Corporation, Kawasaki, Japan.

